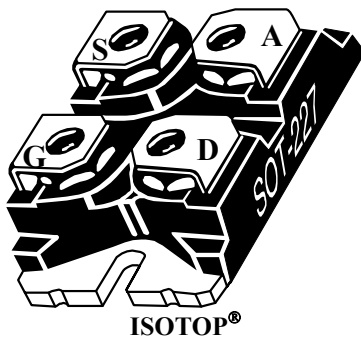
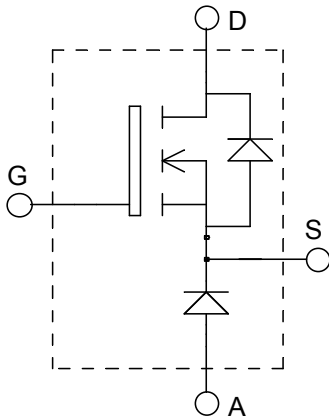


**ISOTOP[®] Buck chopper
 MOSFET + SiC chopper diode
 Power module**

**$V_{DSS} = 1000V$
 $R_{DSon} = 330m\Omega$ typ @ $T_j = 25^\circ C$
 $I_D = 26A$ @ $T_c = 25^\circ C$**


Application

- AC and DC motor control
- Switched Mode Power Supplies

Features

- **Power MOS 8TM MOSFET**
 - Low R_{DSon}
 - Low input and Miller capacitance
 - Low gate charge
 - Avalanche energy rated
- **SiC Schottky Diode**
 - Zero reverse recovery
 - Zero forward recovery
 - Temperature Independent switching behavior
 - Positive temperature coefficient on VF
- ISOTOP[®] Package (SOT-227)
- Very low stray inductance
- High level of integration

Benefits

- Outstanding performance at high frequency operation
- Stable temperature behavior
- Very rugged
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Easy paralleling due to positive TC of VCEsat
- RoHS Compliant

Absolute maximum ratings

Symbol	Parameter	Max ratings	Unit
V_{DSS}	Drain - Source Breakdown Voltage	1000	V
I_D	Continuous Drain Current	$T_c = 25^\circ C$	26
		$T_c = 80^\circ C$	20
I_{DM}	Pulsed Drain current	140	A
V_{GS}	Gate - Source Voltage	± 30	V
R_{DSon}	Drain - Source ON Resistance	396	m Ω
P_D	Maximum Power Dissipation	$T_c = 25^\circ C$	543
I_{AR}	Avalanche current (repetitive and non repetitive)	18	A

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com

All ratings @ $T_j = 25^\circ\text{C}$ unless otherwise specified

Electrical Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 1000\text{V}$ $V_{GS} = 0\text{V}$	$T_j = 25^\circ\text{C}$		100	μA
			$T_j = 125^\circ\text{C}$		500	
$R_{DS(on)}$	Drain – Source on Resistance	$V_{GS} = 10\text{V}, I_D = 18\text{A}$		330	396	$\text{m}\Omega$
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS} = V_{DS}, I_D = 2.5\text{mA}$	3	4	5	V
I_{GSS}	Gate – Source Leakage Current	$V_{GS} = \pm 30\text{V}$			± 100	nA

Dynamic Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
C_{iss}	Input Capacitance	$V_{GS} = 0\text{V}$ $V_{DS} = 25\text{V}$ $f = 1\text{MHz}$		7868		pF
C_{oss}	Output Capacitance			825		
C_{riss}	Reverse Transfer Capacitance			104		
Q_g	Total gate Charge	$V_{GS} = 10\text{V}$ $V_{Bus} = 500\text{V}$ $I_D = 18\text{A}$		305		nC
Q_{gs}	Gate – Source Charge			55		
Q_{gd}	Gate – Drain Charge			145		
$T_{d(on)}$	Turn-on Delay Time	Resistive switching @ 25°C $V_{GS} = 15\text{V}$ $V_{Bus} = 667\text{V}$ $I_D = 18\text{A}$ $R_G = 2.2\Omega$		44		ns
T_r	Rise Time			40		
$T_{d(off)}$	Turn-off Delay Time			150		
T_f	Fall Time			38		

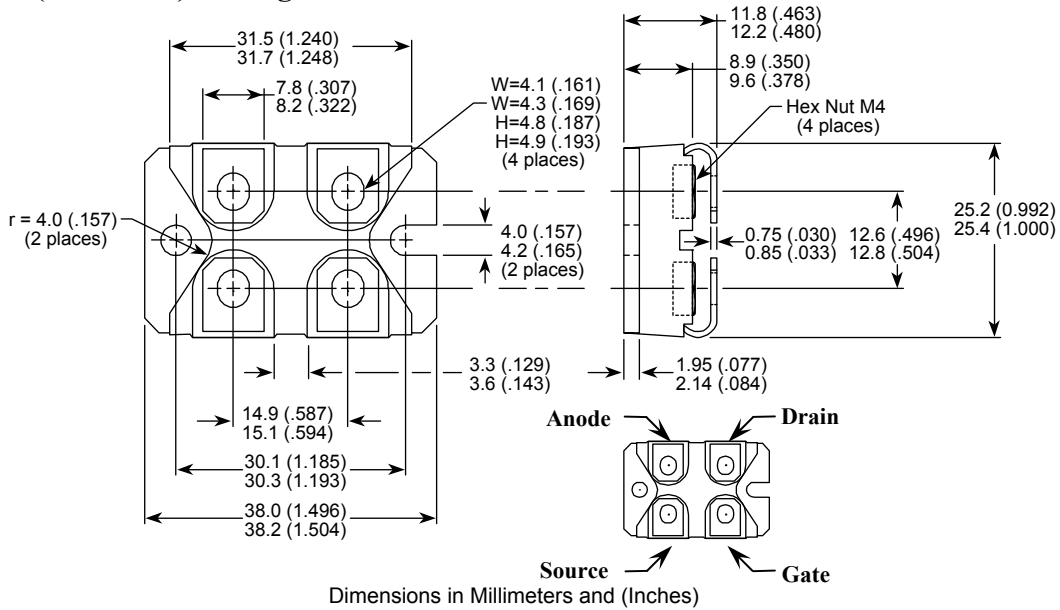
SiC chopper diode ratings and characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
V_{RRM}	Maximum Peak Repetitive Reverse Voltage		1200			V
I_{RM}	Maximum Reverse Leakage Current	$V_R = 1200\text{V}$	$T_j = 25^\circ\text{C}$	32	200	μA
			$T_j = 175^\circ\text{C}$	56	1000	
I_F	DC Forward Current	$T_c = 100^\circ\text{C}$		10		A
V_F	Diode Forward Voltage	$I_F = 10\text{A}$	$T_j = 25^\circ\text{C}$	1.6	1.8	V
			$T_j = 175^\circ\text{C}$	2.3	3	
Q_C	Total Capacitive Charge	$I_F = 10\text{A}, V_R = 600\text{V}$ $di/dt = 500\text{A}/\mu\text{s}$		80		nC
C	Total Capacitance	$f = 1\text{MHz}, V_R = 200\text{V}$		96		pF
		$f = 1\text{MHz}, V_R = 400\text{V}$		69		

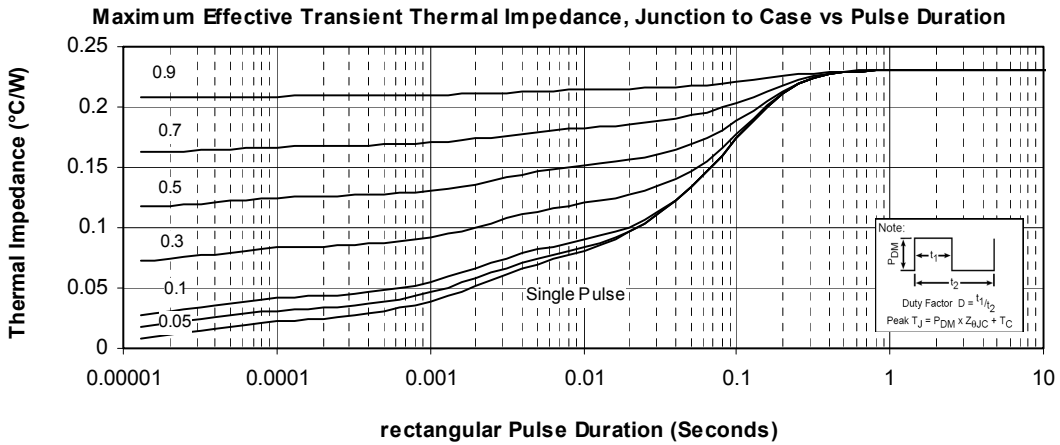
Thermal and package characteristics

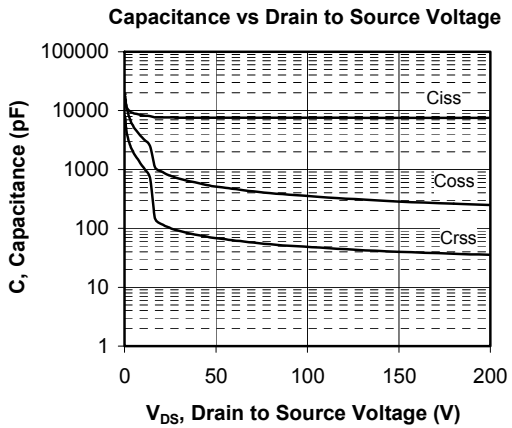
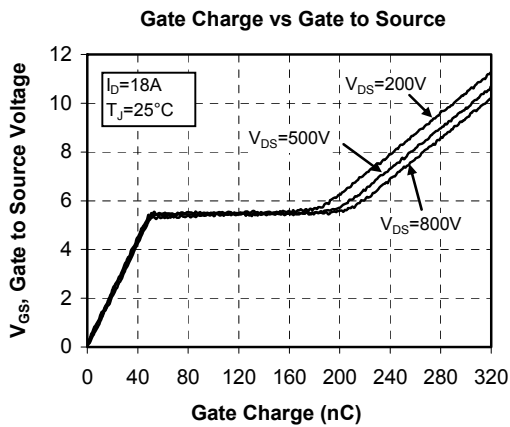
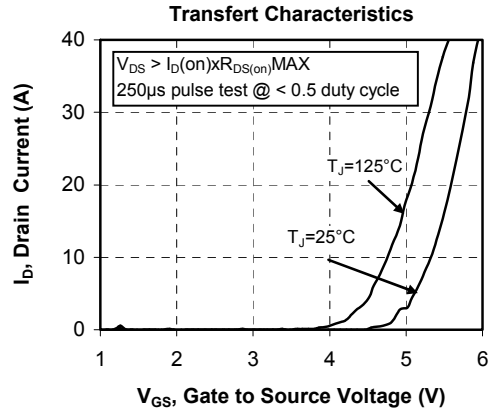
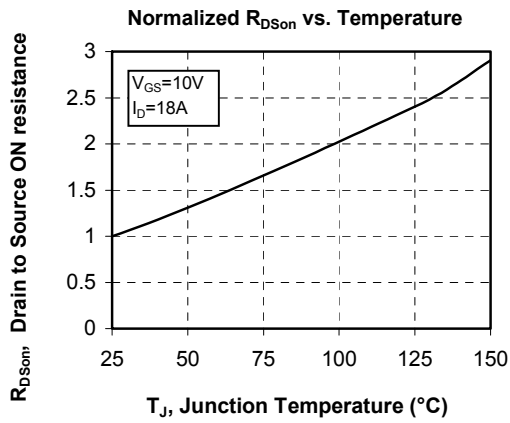
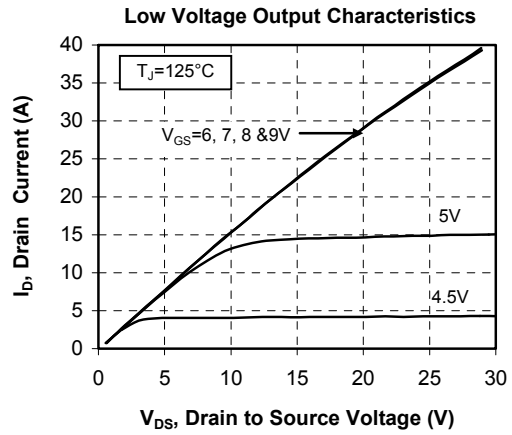
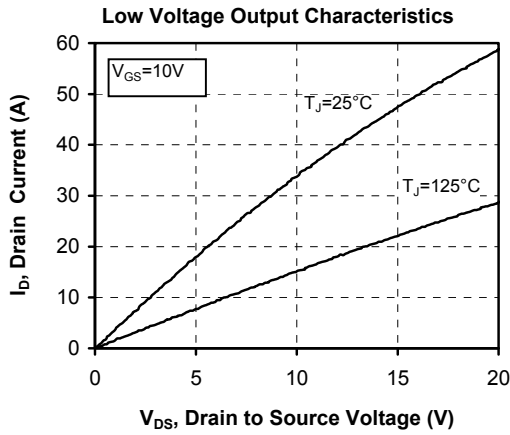
Symbol	Characteristic	Min	Typ	Max	Unit
R_{thJC}	Junction to Case Thermal Resistance	Mosfet		0.23	$^\circ\text{C}/\text{W}$
		SiC Diode		1.65	
R_{thJA}	Junction to Ambient (IGBT & Diode)			20	
V_{ISOL}	RMS Isolation Voltage, any terminal to case $t = 1\text{min}, 50/60\text{Hz}$	2500			V
T_J, T_{STG}	Storage Temperature Range	-40		150	$^\circ\text{C}$
T_L	Max Lead Temp for Soldering: 0.063" from case for 10 sec			300	
Torque	Mounting torque (Mounting = 8-32 or 4mm Machine and terminals = 4mm Machine)			1.5	N.m
Wt	Package Weight		29.2		g

SOT-227 (ISOTOP®) Package Outline

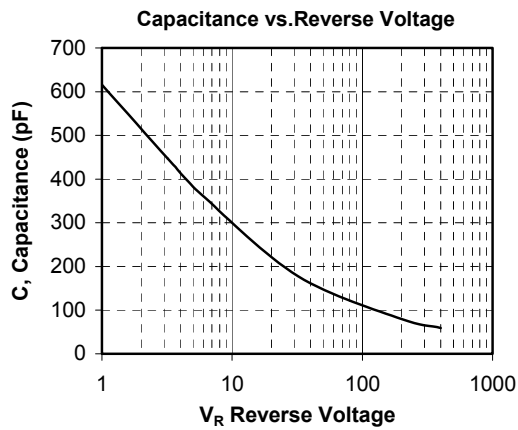
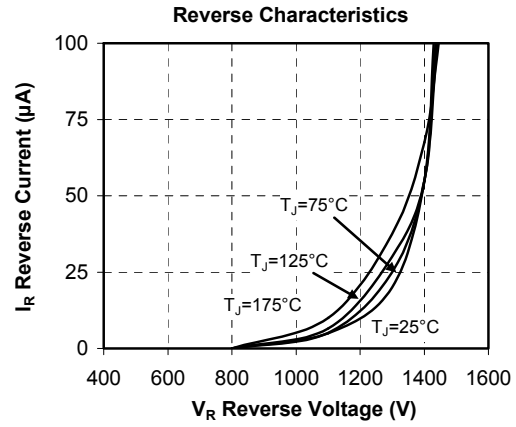
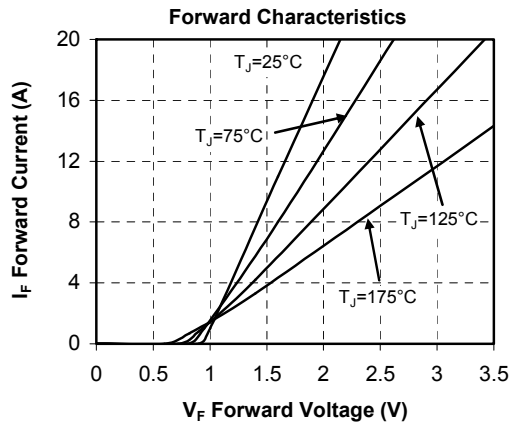
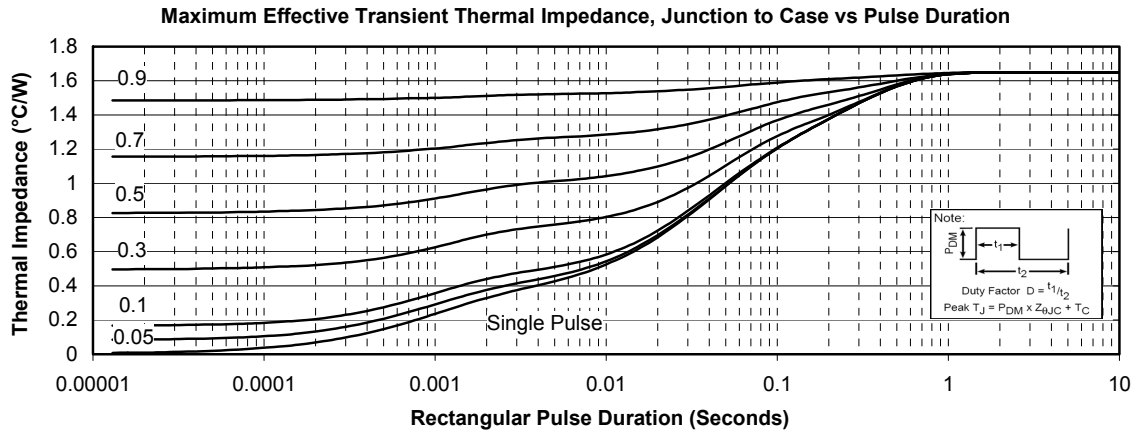


Typical Mosfet Performance Curve





Typical SiC Diode Performance Curve



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